

Silicon Diode

1N4935GP

200V / 1A

DATASHEET

OEM – General Semiconductor

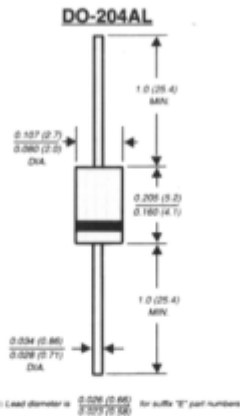
Source: General Semiconductor Databook 1998

1N4933GP THRU 1N4937GP

GLASS PASSIVATED JUNCTION FAST SWITCHING RECTIFIER

Reverse Voltage - 50 to 600 Volts Forward Current - 1.0 Ampere

PATENTED*



Dimensions in inches and (millimeters)
 * Glass-plastic encapsulation is covered by
 Patent No. 3,996,602 and brazed-lead assembly by Patent No. 3,930,306



FEATURES

- ◆ Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- ◆ High temperature metallurgically bonded construction
- ◆ Capable of meeting environmental standards of MIL-S-19500
- ◆ For use in high frequency rectifier circuits
- ◆ Fast switching for high efficiency
- ◆ Glass passivated cavity-free junction
- ◆ 1.0 Ampere operation at $T_A=75^{\circ}\text{C}$ with no thermal runaway
- ◆ Typical I_R less than $0.1\mu\text{A}$
- ◆ High temperature soldering guaranteed: $350^{\circ}\text{C}/10$ seconds, $0.375''$ (9.5mm) lead length, 5 lbs. (2.3kg) tension

MECHANICAL DATA

Case: JEDEC DO-204AL molded plastic over glass body
Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026
Polarity: Color band denotes cathode end
Mounting Position: Any
Weight: 0.012 ounce, 0.34 gram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

	SYMBOLS	1N 4933GP	1N 4934GP	1N 4935GP	1N 4936GP	1N 4937GP	UNITS
* Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	Volts
* Maximum RMS voltage	V_{RMS}	35	70	140	280	420	Volts
* Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	Volts
* Maximum average forward rectified current 0.375" (9.5mm) lead length at $T_A=75^{\circ}\text{C}$	$I_{(AV)}$	1.0					Amp
* Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	30.0					Amps
* Maximum instantaneous forward voltage at 1.0A	V_F	1.2					Volts
* Maximum DC reverse current $T_A=25^{\circ}\text{C}$ at rated DC blocking voltage $T_A=125^{\circ}\text{C}$	I_R	5.0 100.0					μA
* Maximum reverse recovery time (NOTE 1)	t_{rr}	200.0					ns
Typical junction capacitance (NOTE 2)	C_J	15.0					pF
Typical thermal resistance (NOTE 3)	$R_{\theta JA}$	55.0					$^{\circ}\text{C}/\text{W}$
* Operating junction and storage temperature range	T_J, T_{STG}	-65 to +175					$^{\circ}\text{C}$

NOTES:
 (1) Reverse recovery test conditions: $I_F=1.0\text{A}$, $V_R=30$ Volts
 (2) Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts
 (3) Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted
 * JEDEC registered values

RATINGS AND CHARACTERISTIC CURVES 1N4933GP THRU 1N4937GP

